

# Single-Port IEEE 802.3af/at PSE Controller

### 1. Description

The MK3614E is a high-density integrated autonomous single Ethernet port power sourcing equipment (PSE) controller designed for use in IEEE 802.3af/at Power over Ethernet (PoE) systems. The device provides powered device (PD) detection, classification, current limit, load disconnect detection, and operating current levels. The device features intelligent protection circuitry and allows the delivered to PD power up to 35W. The device integrates a  $0.3\Omega$  power MOSFET and a current-sensing resistor, which enables the non-PoE protocol adapter to be feasibly retrofitted into a PSE adapter with the PoE protocol only requiring a few external components.

The MK3614E's LED pin is an open-drain output. The pin outputs simple digital logic signals, which indicate various operating statuses and fault conditions. The device supports Midspan or Endpoint mode. The Midspan mode function has a longer detection back-off timer.

### 2. Applications

- IEEE 802.3af and 802.3at Power-Sourcing Equipment (PSE)
- Power over Ethernet Switches/Routers
- IP Phone Systems
- IP Camera Systems
- 5G Small Cells

### 3. Features

- IEEE 802.3af and 802.3at compatible
- Fully autonomous operation, no external controller required
- Up to 35W for PSE Applications
- 0.2mA standby current (Midspan mode)
- Integrated an 80V 0.3Ω power MOSFET and current-sensing resistor
- Multi-point detection
- Class 3 and Class 4 configuration
- Supports reset operation
- LED status indication
- Supports Midspan and Endpoint modes
- 8-pin ESOP-8 package with thermal pad

# 4. Typical Application

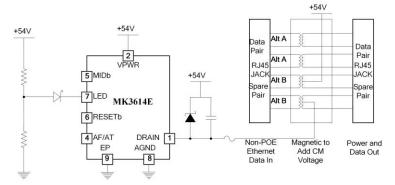


Figure 1. Typical Application Diagram for 802.3at Midspan Configuration



# 5. Order Information

Order Part Number	Descriptions
MK3614EXAD	ESOP-8, tape, 4k/reel

# 6. Pin Configuration and Functions

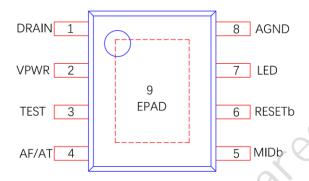


Figure 2. Pin Function (top view)

**Table 1. Pin Functions** 

	Pin I/O		1/0	Description
ı	NO.	Name	1/0	Description
	1	DRAIN	Analog Power Output	MOSFET drain output.
	2	VPWR	Analog Power Input Positive PoE voltage (+44V to 57V) relative to AGND.	
	3	TEST	<ul><li>Connect to AGND.</li></ul>	
	4	AF/AT	Digital Input	Pull up to internal VDD rail with 10µA current. Connect to AGND for AF configuration, leave floating for AT configuration.
	5	MIDb	Digital Input	Pull up to internal VDD rail with $10\mu A$ current. Connect to AGND to set 2.7 seconds detection backoff timing (Midspan), leave floating for Endpoint configuration.
	6	RESET	Digital Input	Pull up to internal VDD rail with $20\mu A$ current. Active low device reset input. Connect a $120k\Omega$ to $200k\Omega$ resistor to AGND.
	7 LED Digital Output		Digital Output	Open drain output pin, turn on an external LED when a PoE PD is connected and powered. Refer to LED section for more details.
	8	AGND	Analog Ground	Analog ground.
	9	EPAD	_	Exposed pad, it should be connected to AGND, connect to power ground plane for better thermal performance.



# 7. Specifications

### 7.1 Absolute Maximum Ratings (1)

		MIN	MAX	Units
	VCC VPWR, DRAIN to AGND	-0.3	80	
Input voltages	LED to AGND	-0.3	35	V
	TEST, AF/AT, RESETb, MIDb to AGND	-0.3	7	5
Operating Junction Temperature,		-40	150	
Storage Temperature, T <sub>stg</sub>		-65	160	$^{\circ}$
Soldering Temperature (10 second), T <sub>sld</sub>		660	260	

### Note:

(1) Stresses beyond the "ABSOLUTE MAXIMUM RATINGS" may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated in "RECOMMENDED OPERATING CONDITIONS". Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

### 7.2 ESD Ratings

	· · · · ·	Value	Units
Electrostatic	Human body model (HBM), per ANSI/ESDA/JEDEC JS-001	500	V
discharge V <sub>ESD</sub>	Charged device model (CDM), per JEDEC specification JESD22-C101 <sup>(2)</sup>	2000	V

### Notes:

- JEDEC document JEP155 states that 500V HBM allows safe manufacturing with a standard ESD control process
- JEDEC document JEP157 states that 250V CDM allows safe manufacturing with a standard ESD control process



### 7.3 Recommended Operating Conditions

		MIN	MAX	Units
Recommended Operation Conditions	VPWR, DRAIN to AGND	32	60	
	LED to AGND	0	30	
	TEST, AF/AT, MIDb, RESETb, MIDb	0	5.5	]
	to AGND			(4
	Junction Temperature	-40	+125	(C)

### 7.4 Thermal Information

		Value	Units
Package Thermal Resistance	$\theta_{JA}$ (Junction to ambient)	30	°C/W
, actago meman recicalise	$\theta_{JC}$ (Junction to case)	10	

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### 7.5 Electrical Characteristics

Conditions are  $-40^{\circ}\text{C} < \text{T}_{\text{J}} < 125~^{\circ}\text{C}$ ,  $\text{V}_{\text{PWR}}$  = 54 V unless otherwise noted. Typical values are at 25 °C. All voltages are with respect to AGND unless otherwise noted.

Parameter		Test Conditions	MIN	TYP	MAX	UNIT
Power Supply Volta	ages					
Vuvlo_on	V <sub>PWR</sub> UVLO Input Voltage		25.5	28	- (	V
Vuvlo_off	V <sub>PWR</sub> UVLO Input Voltage			31	33.5	V
Power Supply Curr	ents <sup>(1)</sup>			6	<i>O.</i>	
lewr	V <sub>PWR</sub> Supply	During normal operation (Detection + Idle), MIDb=Float	-	0.45	_	mA
TI WIX	Current	During normal operation (Detection + Idle), MIDb=GND	50	0.2	_	mA
Detection Specifica	ations		0			
I <sub>DET_SC</sub>	Detection Short Circuit Current	Measured when DRAIN is shorted to VPWR	_	1.5	5	mA
V	Detection Voltage When R <sub>DET</sub> = 24	V <sub>PWR</sub> - V <sub>DRAIN</sub> , primary detection voltage	2.8	4	_	V
Vport	kΩ	V <sub>PWR</sub> - V <sub>DRAIN</sub> , secondary detection voltage	l	8	10	V
T <sub>DET</sub>	Detection Time			320	500	ms
Tidle	Detection Idle	MIDb=Float	_	315	_	ms
TIDLE	Time	MIDb=GND		2700		ms
R <sub>GOOD</sub> <sup>(1)</sup>	Signature Resistance		l	25	_	kΩ
Rdet_min <sup>(1)</sup>	Minimum Signature Resistance @ PD		15	17	19	kΩ
R <sub>DET_MAX</sub> (1)	Maximum Signature Resistance @ PD		26.5	30	33	kΩ
Скејест	Reject Signature Capacitance		_	2.2	10	μF
Classification Spec	cifications					
VCLASS	Class Event Voltage	V <sub>PWR</sub> - V <sub>DRAIN</sub> , Class current between 0 and 51 mA	15.5	_	20.5	V



			l			1
Iclass_lim	Class Event	Measured when DRAIN is	51	_	95	mA
	Current Limitation	shorted to VPWR				
T <sub>CLE</sub>	Class Event	Assigned PD Class 0, 1, 2, 3,	6	_	30	ms
	Timing	4				
		Class Signature 0	0	_	5	mA
		Threshold between Class	5	_	8	mA
		Signature 0 or 1	_			-1)
		Class Signature 1	8	_	13	mA
		Threshold between Class	13	_	16	mA
		Signature 1 or 2	10			1117 (
	Classification	Class Signature 2	16		21	mA
ICLASS_REGION	Current Region	Threshold between Class	21		25	mA
	Current Negion	Signature 2 or 3	21	5	25	ША
		Class Signature 3	25	_	31	mA
		Threshold between Class	24		25	A
		Signature 3 or 4	31	_	35	mA
		Class Signature 4	35	_	45	mA
		Threshold between Class	45	_	54	
		Signature 4 or invalid Class	45		51	mA
Classification Mark	Specifications	14				
	Mark Event	V <sub>PWR</sub> - V <sub>DRAIN</sub> , Mark current	_			
Vmark	Voltage	between 0 and 5 mA	7	_	10	V
	Mark Event	Measured when DRAIN is			0.5	
I <sub>MARK_LIM</sub>	Current Limitation	shorted to VPWR	51	_	95	mA
_	Mark Event					
$T_ME$	Timing	Assigned PD Class 4	6	_	12	ms
Current Limit and (	Overcurrent					
	Overcurrent	TA=25°C, AF/AT=0b	_	410		mA
Ісит	Threshold	TA=25°C, AF/AT=1b	_	710	_	mA
- 0	Overcurrent Time					
Тсит	Limit		50	_	75	ms
(7)	Output Current in	<b></b>				
Inrush	POWER_UP	TA=25°C, all assigned PD	_	465	_	mA
	State	Classes, V <sub>PORT</sub> > 30 V				
7		TA=25°C, Power-on, assigned		45-		_
		PD Class 0, 1, 2, 3	_	485	_	mA
ILIM	Current Limit	TA=25°C, Power-on, assigned				
		PD Class 4	_	825	_	mA
h .						



-	Short Circuit Time	Power-on, assigned PD Class 0, 1, 2, 3	50	_	75	ms
Тым	Limit	Power-on, assigned PD Class 4	10	_	75	ms
Load Disconnect						
IPORT_DIS	DC MPS Current	Current per pairset	_	7.5	10	mA
T <sub>MPDO</sub>	PD MPS Dropout Time Limit		300	_	400	ms
MOSFET On Resist	tance				(	
R <sub>DSON</sub>	FET Resistance	100mA drain to source current		290		mΩ
Digital Pin Charact	eristics			X		
VIL	Input Low Voltage	AF/AT, RESETb, MIDb			1	V
V <sub>IH</sub>	Input High Voltage	AF/AT, RESETb, MIDb	2	5.		V
ILK	Input Leakage	AGND < VIN < VDD, AF/AT, RESETb, MIDb	1	_	1	μA
l <sub>PU</sub>	Pullup Current to VDD	AF/AT, MIDb = 0V	-13	-10	-7	μA
l <sub>PU</sub>	Pullup Current to VDD	RESETb = 0V	-26	-20	-14	μΑ
Over Temperature	Protection (1)					
T <sub>RISE</sub>	Rising Threshold		_	150	_	$^{\circ}$ C
TFALL	Recover Threshold	0,	_	130	_	${\mathbb C}$

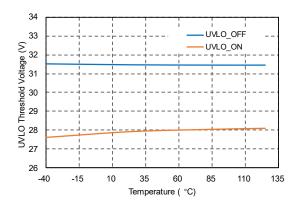
### Note:

<sup>(1)</sup> Values are verified by characterization on bench, not tested in production.



# 7.6 Typical Characteristics

Typical values are at  $V_{PWR}$  = 54V, TA = 25°C, Endpoint mode with a Class 0 PD, unless otherwise noted



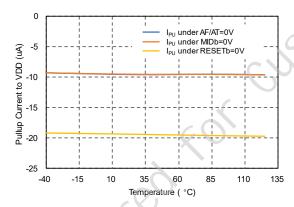
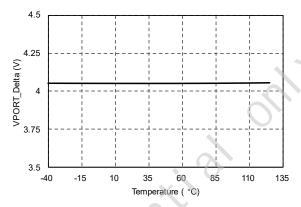


Figure 3. V<sub>PWR</sub> UVLO Threshold Voltage vs. Temperature

Figure 4. Digital Pin Pullup Current to VDD



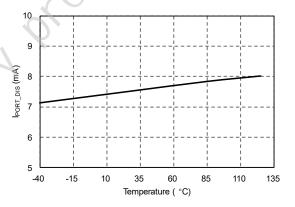


Figure 5. Voltage Difference Between Detection Points vs. Temperature

Figure 6. DC Maintain Power Signature



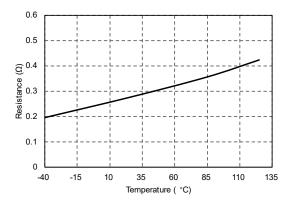


Figure 7. Internal FET Resistance vs. **Temperature** 

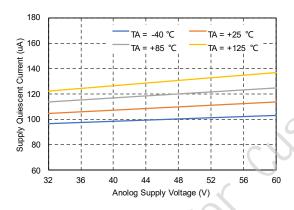


Figure 8. VPWR Current vs. Temperature (RESETb = 0V)

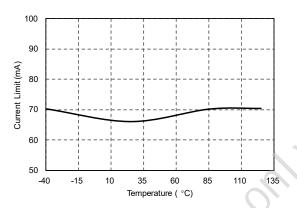


Figure 9. Classification and Mark Current Limit vs. Temperature

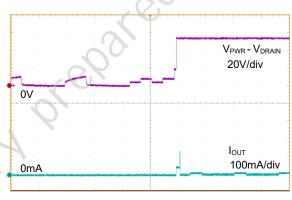


Figure 10. Startup with a valid PD

Time(200ms/div)

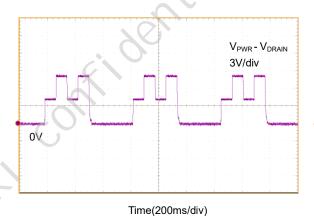


Figure 11. Detection with invalid PD (33k $\Omega$ )

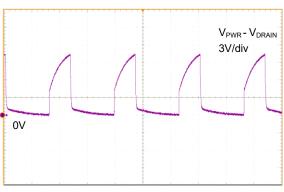
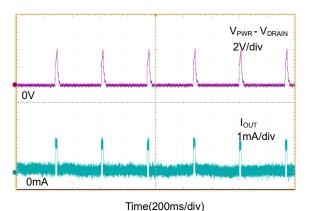


Figure 12. Detection with invalid PD (Open)

Time(200ms/div)



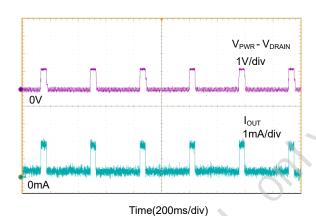


V<sub>PWR</sub> - V<sub>DRAIN</sub>
3V/div

Figure 13. Detection with invalid PD (24k $\Omega$  and 10 $\mu$ F)

Figure 14. Detection with invalid PD (15 $k\Omega$ )

Time(200ms/div)



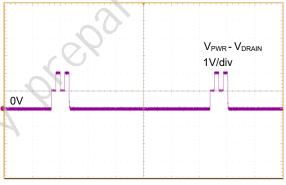
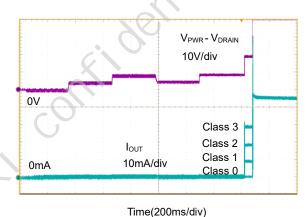


Figure 15. Detection with output shorted

Figure 16. Detection in Midspan with invalid PD (15 $k\Omega$ )

Time(500ms/div)



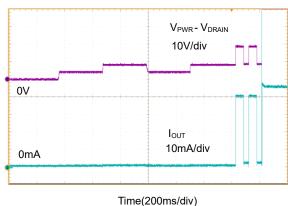


Figure 17. Classification with different PD invalid PD (15kΩ)

Figure 18. Classification with PD Class 4



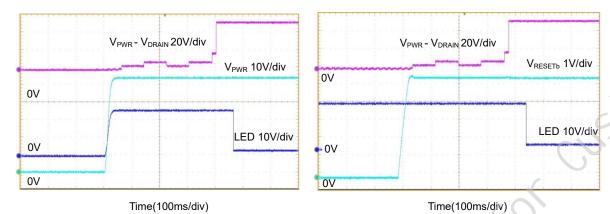
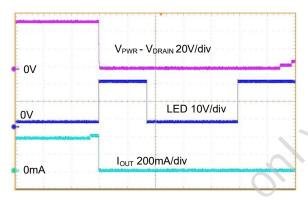


Figure 19. LED function of the PD powered from V<sub>PWR</sub>

Figure 20. LED function of the PD powered from VRESETD



Time(200ms/div)

Figure 21. LED function of ICUT



# 8. Detailed Description

### 8.1 Overview

The MK3614E is a high-density integrated autonomous single-port PSE controller designed for use in IEEE 802.3af/at PoE systems. The device provides PD detection, classification, current limit, load disconnect detection and operating current levels. The MK3614E provides up to 35W to the Ethernet port. Besides, the MK3614E features intelligent protection circuitry including input undervoltage lockout, over-temperature protection, overcurrent timeout, port short protection, load-disconnect detection timeout, port voltage slew-rate limit during startup, operating status, fault conditions indicated by LED.

### 8.2 Functional Block Diagram

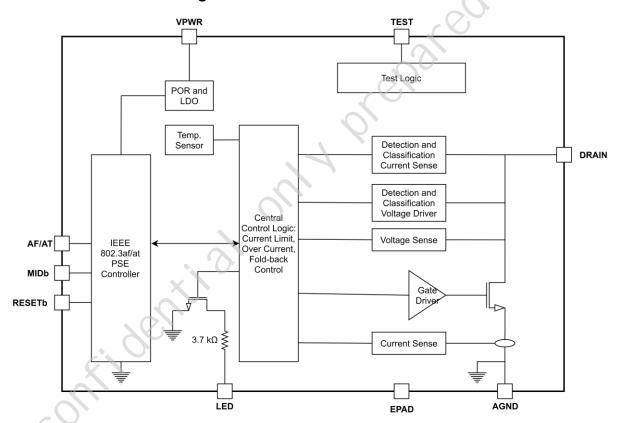


Figure 22. Block Diagram



### 8.3 Feature Description

#### 8.3.1 Reset

The MK3614E is reset by power-up and hardware reset. Reset condition is cleared once V<sub>PWR</sub> rises above the UVLO threshold. The MK3614E's RESETb pin is tied to internal VDD through a pull-up resistance. In a typical application, connect a 120k $\Omega$  to 200k $\Omega$  resister to AGND. However, if the RESETb pin is driven low (> 110us, typ), the MK3614E is reset. Once in the reset state, the port output and LED detection function are disabled. At the end of a reset event, the MK3614E latches in the state of AF/AT and MIDb input signals. During normal operation, changes of the AF/AT and MIDb inputs are ignored, and these inputs can only be changed at any time prior to the end of a reset state.

#### 8.3.2 Midspan Mode

The MK3614E supports an Endpoint or Midspan PSE network configuration. In midspan mode, when failed detections occur, the device waits about 2.7s before attempting to detect again. Like the RESETb pin, MIDb pin is also tied to internal VDD through a pull-up resistance. The device is configured as Endpoint mode by default unless the MIDb pin is driven low.

#### 8.3.3 **PD Detection and Classification**

Detection function of the MK3614E is the most important, which determines if the remote equipment

connected to a PSE is capable of receiving power. To avoid false detection in noisy environments, the MK3614E detects a PD by using a robust 4-point detection algorithm to reliably determine the signature resistance of the PD. During detection phase, the MK3614E keeps the internal MOSFET off and drives probe voltages with two different levels through the DRAIN pin. The device uses a specific algorithm to calculate the PD signature resistance by sampling the current injected into the port. Once the detection result is RGOOD, the MK3614E will perform Physical Layer classification by driving a class probe to determine the PD's class signature. The number of class events and mark events determines the PD requested power. Figure 23 shows a timing diagram of PD detection and classification for a Type 1 PSE powering a Type 1 PD. In this example, the MK3614E produces one class event to a Type 1 PD without any mark event. As shown in Figure 24 two class events and two mark events are driven by the MK3614E for a Type 2 PSE powering a Class 4 PD.

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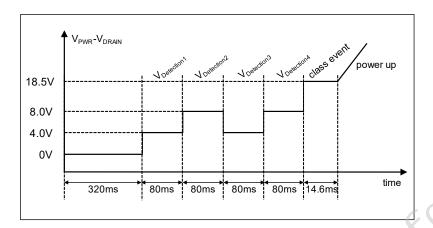


Figure 23. Type 1 Detection, Classification, and Port Power-Up Sequence

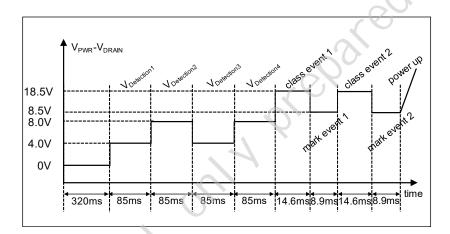


Figure 24. Type 2 Detection, Classification, and Port Power-Up Sequence

### 8.3.4 Inrush

After classification, if the MK3614E decides to power the PD, it will first go through the inrush phase. During inrush, the PSE limits the amount of current being delivered for at least 60ms. Between 1ms and 60ms after power-on, the inrush current of the MK3614E is limited to no more than 700mA

### 8.3.5 Operating Power

During a nominal powering state, the MK3614E checks for abnormal conditions, including overcurrent, PD disconnection, and short-circuits. Meanwhile, the MK3614E assigns the class required for PD to PD. The MK3614E achieves the purpose of distributing power by controlling the current called I<sub>CUT</sub>. Once the current exceeds the I<sub>CUT</sub> as least T<sub>CUT</sub>, the MK3614E immediately cuts off the power and goes through detection phase.

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#### 8.3.6 **Maintain Power Signature**

When the MK3614E is supplying power to a PD, the MK3614E keeps on monitoring the current drawn in order to make sure that the PD is still connected. The minimum current that the PD must draw to avoid being disconnected is named the Maintain Power Signature (MPS). The MK3614E is designed to remove power when the MPS is absent for at least 350ms, ensuring that disconnected cables do not remain powered. In order to further reduce minimum standby power consumption for PoE systems, the MK3614E only requires that PD must draw a current above  $I_{PORT\ DIS}$  for at least  $T_{MPS}$  with no more than  $T_{MPDO}$  between pulses.

#### 8.3.7 **Current Limit and Voltage Foldback**

The MK3614E integrates a current-sensing resistor connected between the internal MOSFET and AGND to monitor the loop current. During normal operating conditions, the current running through the current-sensing resistor never exceeds the threshold ILIM. Otherwise, the internal feedback circuit regulates the driver voltage of the MOSFET to limit the current. Besides, the MK3614E senses the DRAIN voltage and regulates the current-limit value, which helps to reduce the internal MOSFET power dissipation.

#### 8.3.8 **LED Signals**

The MK3614E's LED pin is open-drain output. The pin outputs FM signals with different duty ratios, which indicate various operating statuses and fault conditions. The LED pin can be directly connected to the VIN port through pull -up resistors, but an external pull-down resistor is required to reduce the voltage stress of the LED pin. As shown in Figure 22, the LED pin outputs various signals by controlling the internal MOSFET. Once the MOSFET is turned on, the current is injected to AGND through the internal integrated resistor, where its resistance value is approximately  $3.7k\Omega$ . Figure 25 shows the recommended LED connection circuit.

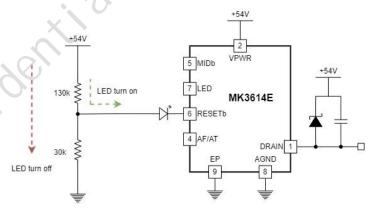


Figure 25. Recommended LED connection circuit

The following table lists LED pin states which indicate various operating statuses and fault conditions of the MK3614E.



### **Table 2. LED pin functions**

LED Indication  LED on  LED off  LED blinking only several times	Status  Port successfully powered at requested power level  Looking for a valid detection signature	Note  The MOSFET that controls the LED output is turn on.  The MOSFET that controls the LED output is turn off.
LED off  LED blinking only	requested power level  Looking for a valid detection signature	on.  The MOSFET that controls the LED output is turn
LED off  LED blinking only	Looking for a valid detection signature	The MOSFET that controls the LED output is turn
LED blinking only	signature	·
LED blinking only		off.
soveral times	Error condition, such as OCP,	The MOSFET that controls the LED output
Several lillies	ICUT, port short fault, OTP	switched on and off several times, then off.
		A prepared for



# 9. Application Examples

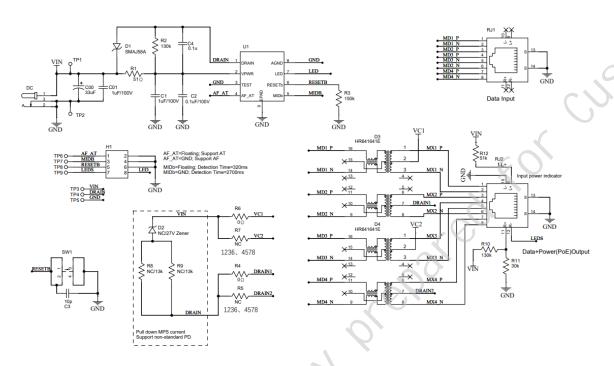


Figure 26. Application Schematic Example

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# 10. Power Supply Recommendations

# 11. Layout

#### 11.1 **Layout Guidelines**

To achieve high performance of the MK3614E, the following layout tips must be followed.

- At least one low-ESR ceramic bypass capacitor for the VPWR pin must be used. Place the capacitor as close as possible to the MK3614E VPWR pin.
- The unidirectional TVS connected between VPWR and DRAIN must be employed to prevent an external lightning strike and surge current from damaging the chip.
- 3. The recommended voltage of the LED pin is not higher than 30V and the current does not exceed 1mA, otherwise it may damage the pin. The pin voltage can be reduced by a pulldown resistor divider.
- TEST pin is recommended to be tied to GND, and thermal pad is used for chip heat dissipation. 4.
- Use short, wide traces whenever possible for high power paths.

#### 11.2 **Layout Example**

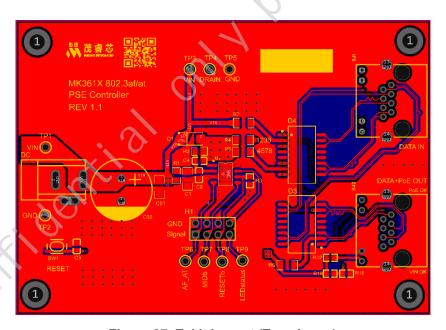


Figure 27. Evkit Layout (Tope Layer)



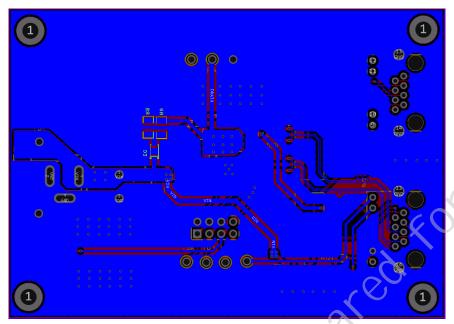


Figure 28. Evkit Layout (Bottom Layer)



# 12. Device and Documentation Support

- 12.1 Device Support
- 12.2 Documentation Support
- 12.3 Receiving Notification of Documentation Updates
- 12.4 Support Resources
- 12.5 Trademarks

### 12.6 Electrostatic Discharge Caution

This integrated circuit can be damaged by ESD. Meraki Integrated recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device to not meet its published specifications.

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# 13. Mechanical, Packaging

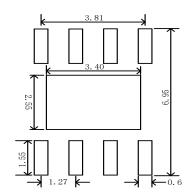


Figure 29. Recommended Land Pattern (mm)

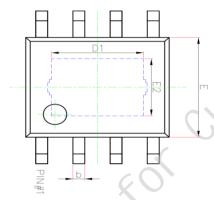


Figure 30. MK3614E Top View

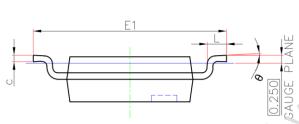


Figure 31. MK3614E Side View

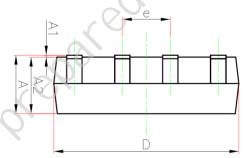


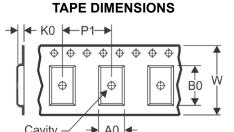
Figure 32. MK3614E Side View

	CVMDOL	Millin	neter	
	SYMBOL	MIN	NOM	
	Α	1.300	1.700	
	A1	0.000	0.100	
	A2	1.350	1.550	
	b	0.330	0.510	
	С	0.170	0.250	
	D	4.700	5.100	
	D1	3.050	3.250	
•	Е	3.800	4.000	
	E1	5.800	6.200	
	E2	2.160	2.360	
<b>(</b> 0	е	1.270(	BSC)	
	L	0.400	1.270	
	θ	0°	8°	



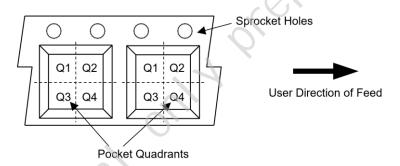
# 14. Reel and Tape Information

# **REEL DIMENSIONS** Reel Diameter Reel Width(W1)



Α0	Dimension designed to accommodate the component width
В0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

### **QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE**



Device	Package	Pins	Quantities	Reel Diameter	Reel Width
	Type			(mm)	W1(mm)
MK3614E	ESOP8	8	4000	330	12.4
A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1
					Quadrant
6.4	5.4	2.1	8.0	12.0	Q1

Chexolusia



# 15. Tape and Reel Box Dimensions

